

**Silicon NPN Power Transistors**

**2SC4350**

**DESCRIPTION**

- With TO-220 package
- High DC current gain
- DARLINGTON

**APPLICATIONS**

- For high speed power switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

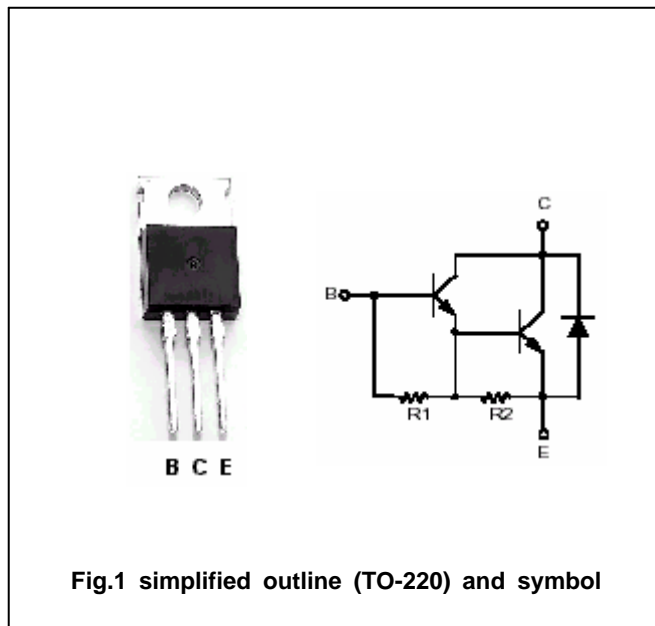


Fig.1 simplified outline (TO-220) and symbol

**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	100	V
$V_{CEO}$	Collector-emitter voltage	Open base	100	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		10	A
$I_B$	Base current		0.5	A
$P_C$	Collector power dissipation	$T_C=25$	40	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

## Silicon NPN Power Transistors

## 2SC4350

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A ; I <sub>B</sub> =0	100			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA; I <sub>E</sub> =0;	100			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =5mA; I <sub>C</sub> =0;	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A; I <sub>B</sub> =5mA			1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A; I <sub>B</sub> =5mA			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V ; I <sub>E</sub> =0			1	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			5.0	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =2V	2000		20000	

◆ h<sub>FE</sub> classifications

M	L	K
2000-5000	4000-10000	8000-20000

Silicon NPN Power Transistors

2SC4350

PACKAGE OUTLINE

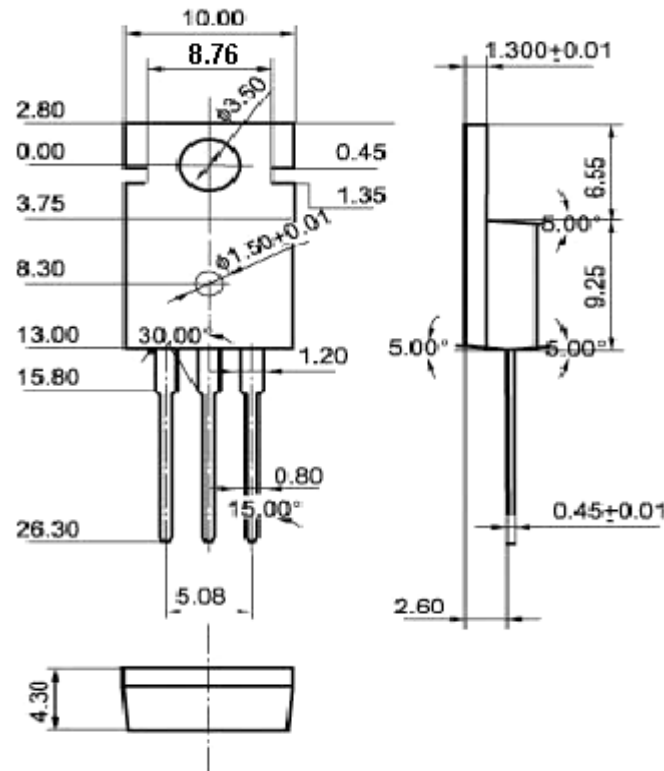


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)